

**1Mx4 Dynamic RAM
CMOS, Monolithic**

The EDI441024C is a fast page mode 4096K bit high performance, low power CMOS Dynamic RAM organized as 1024Kx4. The use of four-layer poly process, combined with silicide technology and a single transistor dynamic storage cell, provide high circuit density with high performance.

The use of dynamic circuitry, including sense amplifiers, assures low power dissipation.

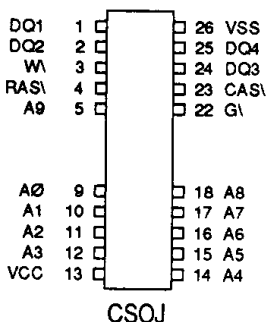
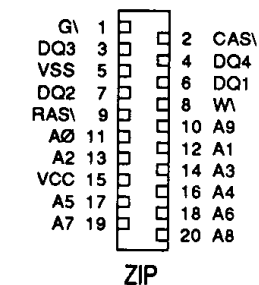
Multiplexed address inputs permit a low pin count for maximum system density.

In addition to the RAS\-only refresh mode, the hidden refresh mode and CAS\ before RAS\ refresh mode are available.

All inputs and outputs are TTL compatible and operate from a single 5 volt supply.

Military product compliant to MIL-STD-883, paragraph 1.2.1, is available.

**Pin Configurations
and Block Diagram**



ADVANCE INFORMATION

Features

1Mx4 bit CMOS Dynamic Random Access Memory

- Access Times 80, 100, 120, and 150ns
- Low Operating Power Dissipation
- Low Standby Power
- Common I/O
- All Inputs/Outputs TTL Compatible

Available in Two Package Styles

- 20 pin Ceramic ZIP, No.18
- 20(26) Lead Ceramic SOJ, No. 16

Single +5V ($\pm 10\%$) Supply Operation

Pin Names

A0-A9	Address Inputs
CAS\	Column Address Strobe
RAS\	Row Address Strobe
W1	Write Control Input
G1	Output Enable
DQ1-DQ4	Data Inputs/Outputs
VCC	Power (+5V $\pm 10\%$)

